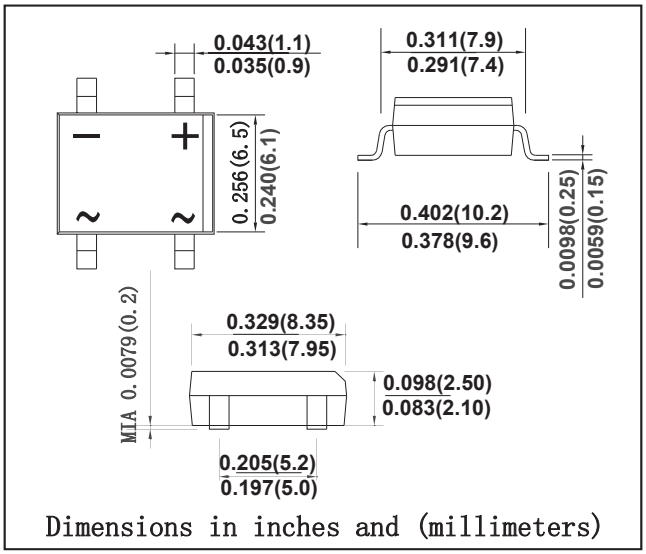
DBS SILICON BRIDGE RECTIFIERV

FEATURES

- The plastic package carries Underwrites Laboratory Flammability Classification 94V-0
- Construction utilizes void-free molded plastic technique
- High reliability
- High temperature soldering guaranteed:260 ℃/10 seconds at terminals
- Component in accordance to RoHs 2015/863 and WEEE 2012/19/EU

MECHANICAL DATA

- Case style: DBS molded plastic
- Mounting position: Any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 ℃ ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

TYPE NUMBER		Symbols	DB151	DB152	DB153	DB154	DB155	DB156	DB157	Units
Maximum Recurrent Peak Reverse Voltage		V_{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage		V_{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage		V_{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Rectified Current		$I_{(AV)}$	1.5							Amp
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		I_{FSM}	50							Amps
Maximum Instantaneous Forward Voltage at 1. 5A DC		V_F	1.1							Volts
Maximum DC Reverse Current at rated DC blocking voltage	T_A=25 ℃	I_R	10							μA
	T_A=125 ℃		500							
Typical junction capacitance(Note1)		C_J	25							pF
Typical thermal resistence(Note 2) Operating		$R_{\theta JA}$	40							K/W
junction and storage temperature range		T_J T_{STG}	-55 to +150							℃

RATINGS AND CHARACTERISTIC CURVES

FIG.1-TYPRCAL FORWARD CURRENT DERATING CURVE

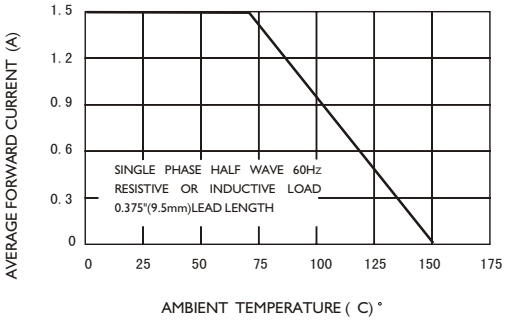


FIG.2-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

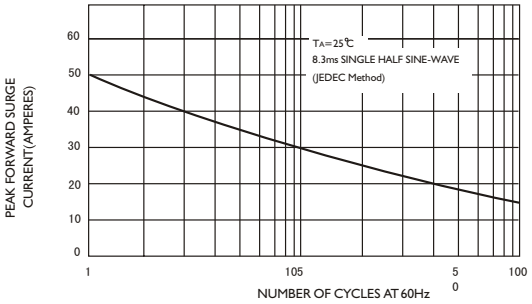


FIG.3-TYPICAL JUNCTION CAPACITANCE

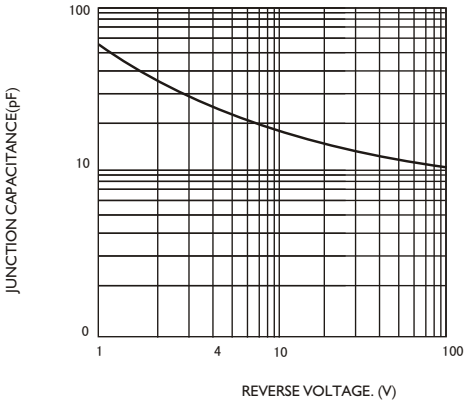


FIG.4-TYPICAL FORWARD CHARACTERISTICS

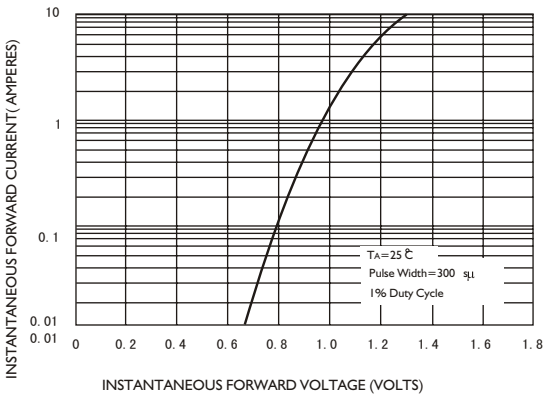


FIG.5-TYPICAL REVERSE CHARACTERISTICS